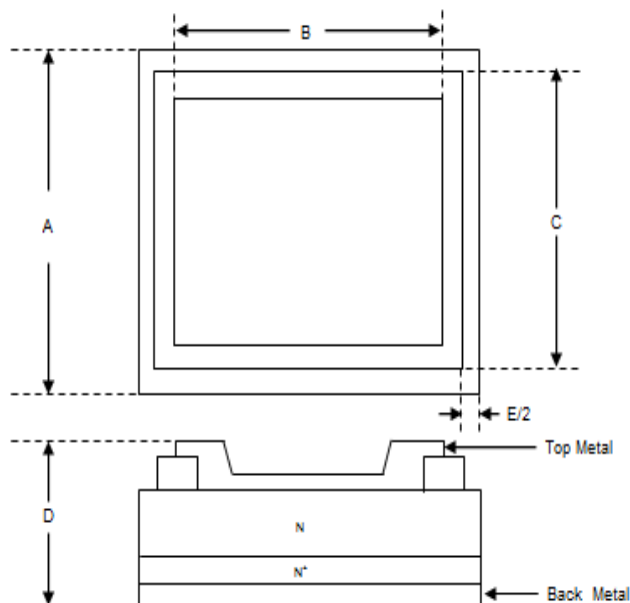


Planar MOS-Controlled Diode Wafer (PMCD)



| Item | Dimensions | |
|------------------------|------------|------|
| | um | mil |
| Die Size (A) | 1830 | 72 |
| Top Metal Pad Size (B) | 1675 | 65.9 |
| Passivation Seal (C) | 1760 | 69.3 |
| Wafer Thickness (D) | 260 | 10.2 |
| Scribe Line Width (E) | 70 | 2.76 |
| Other Informations | | |
| Wafer Size | 6" | |
| Gross Die | 4780 | |
| Top Metal | Al | |
| Back Metal | Ag | |

| Electrical Characteristics @TA=25°C | | | | |
|---------------------------------------------------------------------------------------------------|-----------|-------------------|----------------|---------|
| Item | Symbol | Spec. Limit | Die Sort | Unit |
| Maximum Repetitive Peak Reverse Voltage @0.3mA | V_{RRM} | 45 | 51 | V |
| Maximum Average Forward Rectified Current | I_O | 10 | - | A |
| Forward Voltage Drop, @ $I_F=2A$ @ $I_F=5A$ @ $I_F=10A$ | V_F | - 0.49 0.59 | 0.39 - - | V |
| Maximum Reverse Current at Rated V_{RRM} | I_R | 100 | 70 | μA |
| Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method) | I_{FSM} | 120 | - | A |
| Operating Temperature Range | T_J | -50 to +150 | - | °C |
| Storage Temperature Range | T_{STG} | -50 to +150 | - | °C |
| ESD(IEC61000-4-2) | Contact | 15 | - | KV |